EXHIBIT 3

WHAT IS CLAIMED IS:

1. A gaseous composition at a temperature below about 200°C at atmospheric pressure, adapted to deposit at least a first layer of tin oxide and silicon oxide onto glass at a rate of deposition greater than about 350Å/sec. at a temperature below about 200°C, at atmospheric pressure, wherein the composition comprises a precursor of tin oxide, a precursor of silicon oxide, an accelerant selected from the group consisting of organic phosphites, organic borates and water, and mixtures thereof, and a source of oxygen.

2. The composition of claim 1 wherein the substrate is transparent flat glass at a temperature of from about 450 to about 650°C.

3. The composition of claim 1 producing a glass article having essentially no reflected color in daylight.

4. The composition of claim 1 wherein the glass substrate is moving and the deposition is continuous.

5. The composition of claim 1 at a temperature below about 175°C.

6. The composition of claim 1 wherein the accelerant is triethyl phosphite.

7. The composition of claim 1 wherein the precursor of the tin oxide is R_nSnX_{4-n}, where R is a straight, cyclic, or branched-chain alkyl, or alkenyl of from one to about six carbons; phenyl, substituted phenyl, or $R'CH_2CH_2$-, where R' is MeO_2C-, EtO_2C-, CH_3CO-, or HO_2C-; X is selected from the group consisting of halogen, acetate, perfluoroacetate, and their mixtures; and where n is 0, 1, or 2.

8. The composition of claim 1 wherein the precursor of the tin oxide is an alkyltin halide.

9. The composition of claim 1 wherein the precursor of the tin oxide is an alkyltin chloride.

10. The composition of claim 1 wherein the precursor of the tin oxide is chosen from the group consisting of monobutylytin trichloride, dibutylytin dichloride, tributylytin chloride, and tin tetrachloride.

11. The composition of claim 1 wherein the precursor of silicon oxide is $R_mO_nSi_p$, where *m* is from 3 to 8, *n* is from 1 to 4, *p* is from 1 to 4, and

R is independently c. ,en from hydrogen and acyl, strai,nt, cyclic, or branched-chain alkyl and substituted alkyl or alkenyl of from one to about six carbons, and phenyl or substituted phenyl.

12. The composition of claim 1 wherein the precursor of silicon oxide is selected from tne group consisting of tetraethylorthosilicate, diacetoxydi-t-butoxysilane, ethyltriacetoxysilane, methyltriacetoxysilane, methyldiacetoxylsilane, tetramethyldisiloxane, tetramethylcyclotetrasiloxane, dipinacoloxysilane, 1,1-dimethylsila-2-oxacyclohexane, tetrakis (1-methoxy-2-propoxy) silane, and triethoxysilane.

13. The composition of claim 1 wherein the precursor of silicon oxide is tetraethylorthosilicate.

14. The composition of claim 1 wherein the accelerant comprises triethyl phosphite.

15. The composition of claim 1 wherein the accelerant comprises triethyl phosphite and triethyl borate.

16. The composition of claim 1 wherein the rate of deposition is greater than about 400Å/sec.

17. The composition of claim 1 wherein the first layer is amorphous.

18. The composition of claim 1 wherein the first layer comprises a plurality of layers, and at least a second layer is deposited on the first layer.

19. The composition of claim 18 wherein the second layer comprises a tin oxide.

20. The composition of claim 18 wherein the second layer comprises a mixture of tin oxide and a fluorine compound.

21. The composition of claim 18 wherein the first layer has a refractive index which changes continuously between the substrate and the second layer.

22. The composition of claim 18 wherein the second layer comprises a doped tin oxide.

23. The composition of claim 18 wherein the second layer is deposited from a precursor mixture comprising monobutyltin trichloride and a fluorine-containing material.

24. The composition of claim 18 wherein the first layer is deposited from a precursor mixture comprising monobutyltin trichloride and tetraethyl orthosilicate in the presence of triethyl phosphite.

25. A gaseous composition adapted to deposit at least a first layer of tin oxide and silicon oxide onto glass at a temperature below about 200°C, at atmospheric pressure, by the method of depositing at least one amorphous layer onto glass at a rate greater than about 400Å/sec., the layer having a controlled index of refraction, by applying to the glass a mixture of a tin oxide precursor, a silicon oxide precursor, and at least one accelerant chosen from the group consisting of boron and phosphorus esters and water.

26. The composition of claim 25 applied by continuous chemical-vapor deposition of a mixture of monobutyltin trichloride, tetraethylorthosilicate and an accelerant onto a moving glass sheet, wherein the glass is at a temperature of from about 450 to about 650°C.